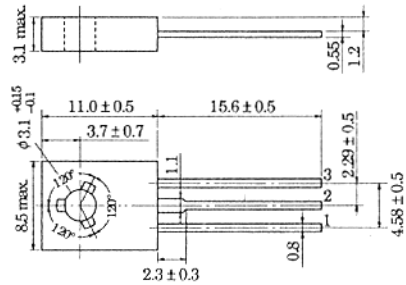
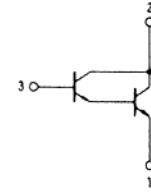


2SC2298

SILICON NPN EPITAXIAL
HIGH GAIN AMPLIFIER



1. Emitter
2. Collector
3. Base
(Dimensions in mm)



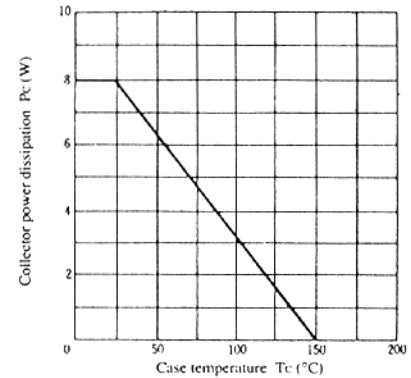
(JEDEC TO-126 MOD.)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SC2298	Unit
Collector to base voltage	V _{CB0}	30	V
Collector to emitter voltage	V _{CEO}	30	V
Emitter to base voltage	V _{EB0}	10	V
Collector current	I _C	1.0	A
Collector peak current	i _{C(peak)}	1.5	A
Collector power dissipation	P _C	0.8	W
	P _{C*}	8	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* Value at T_c = 25°C

■ MAXIMUM COLLECTOR DISSIPATION CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _C = 1mA, R _{BE} = ∞	30	—	—	V
Emitter cutoff current	I _{EBO}	V _{EB} = 10V, I _C = 0	—	—	10	μA
DC current transfer ratio	h _{FE1*}	V _{CE} = 3V, I _C = 10mA	4000	—	—	
	h _{FE2*}	V _{CE} = 3V, I _C = 100mA	10000	—	—	
	h _{FE3*}	V _{CE} = 3V, I _C = 400mA (pulse test)	10000	—	—	
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = 400mA, I _B = 0.1mA (pulse test)	—	—	1.5	V
Base to emitter saturation voltage	V _{BE(sat)}		—	—	2.0	V

* The 2SC2298 is grouped by h_{FE} as follows.

